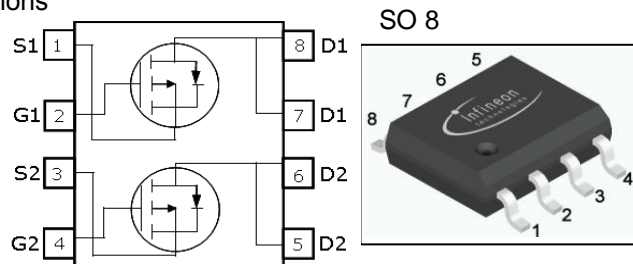


**OptiMOS<sup>®</sup>-P Small-Signal-Transistor**
**Features**

- Dual P-Channel in SO8
- Enhancement mode
- Logic level
- 150°C operating temperature
- Qualified according JEDEC for target applications
- Halogen-free according to IEC61249-2-21
- Pb-free lead plating; RoHS compliant


**Product Summary**

$V_{DS}$		-30	V
$R_{DS(on),max}$	$V_{GS}=-10V$	21	mΩ
	$V_{GS}=-4.5V$	32	
$I_D$		-8.2	A



Type	Package	Marking	Lead free	Halogen free	Packing
BSO303P H	PG-DSO- 8	303P	Yes	Yes	dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value		Unit
			10 secs	steady state	
Continuous drain current <sup>1)</sup>	$I_D$	$T_C=25\text{ °C}$	-8,2	-7,0	A
		$T_C=70\text{ °C}$	-6,6	-5,8	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$	-32,8		
Avalanche energy, single pulse	$E_{AS}$	$I_D=-8.2\text{ A}, R_{GS}=25\text{ }\Omega$	97		mJ
Gate source voltage	$V_{GS}$		$\pm 20$		V
Power dissipation	$P_{tot}$	$T_A=25\text{ °C}$	2		W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150		°C
ESD class		JESD22-A114 HBM	1B (500V - 1kV)		
Soldering temperature			260 °C		
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics</b>						
Thermal resistance, junction - soldering point	$R_{thJS}$		-	-	50	K/W
SMD version, device on PCB:	$R_{thJA}$	minimal footprint, $t < 10s$			110	
		minimal footprint, steady state			150	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , $t < 10s$	-	-	62,5	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , steady state	-	-	80	

**Electrical characteristics**, at  $T_j = 25\text{ °C}$ , unless otherwise specified

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = -250\mu\text{A}$	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -100\mu\text{A}$	-1	-1,5	-2	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 25\text{ °C}$	-	-0,1	-1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_j = 150\text{ °C}$	-	-10	-100	
Gate-source leakage current	$I_{GSS}$	$V_{GS} = -20\text{ V}$ , $V_{DS} = 0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}$ , $I_D = -6.6\text{ A}$	-	25	32	mW
		$V_{GS} = -10\text{ V}$ , $I_D = -8.2\text{ A}$	-	17	21	
Transconductance	$g_{fs}$	$ V_{DS}  > 2 I_D  R_{DS(on)max}$ , $I_D = -6.6\text{ A}$	11	27	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air:  $t \leq 10\text{ sec}$ .

<sup>2)</sup> See figure3 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=-25\text{ V},$ $f=1\text{ MHz}$	-	1785	2678	pF
Output capacitance	$C_{oss}$		-	510	765	
Reverse transfer capacitance	$C_{rss}$		-	425	638	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V}, V_{GS}=-$ $10\text{ V}, I_D=-1\text{ A},$ $R_G=6\ \Omega$	-	11	17	ns
Rise time	$t_r$		-	13	20	
Turn-off delay time	$t_{d(off)}$		-	55	83	
Fall time	$t_f$		-	39	59	

**Gate Charge Characteristics<sup>3)</sup>**

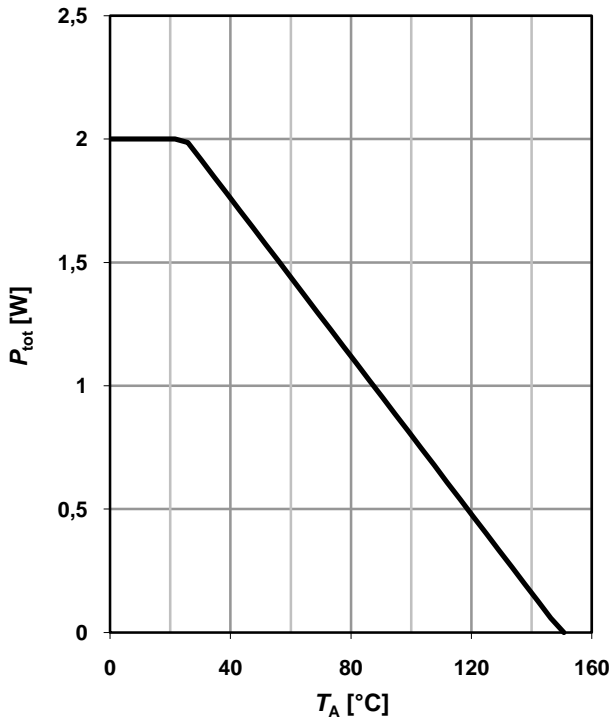
Gate to source charge	$Q_{gs}$	$V_{DD}=-24\text{ V}, I_D=-8.2\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	-5	-6	nC
Gate to drain charge	$Q_{gd}$		-	-14	-20	
Gate charge total	$Q_g$		-	-36	-49	
Gate plateau voltage	$V_{plateau}$		-	-2,7	-	V

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ °C}$	-	-	-2,2	A
Diode direct current, pulsed	$I_{SM}$		-	-	-32,8	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-8.2\text{ A},$ $T_J=25\text{ °C}$	-	-0,9	-1,3	V
Reverse recovery time	$t_{rr}$	$V_R=-15\text{ V}, I_F= I_S ,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	24	36	ns
Reverse recovery charge	$Q_{rr}$		-	13	19	nC

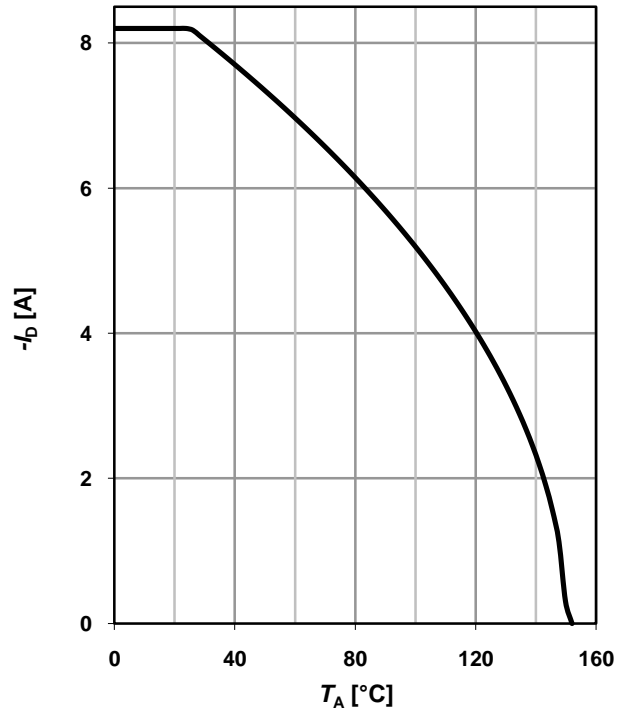
**1 Power dissipation**

$P_{tot}=f(T_A)$



**2 Drain current**

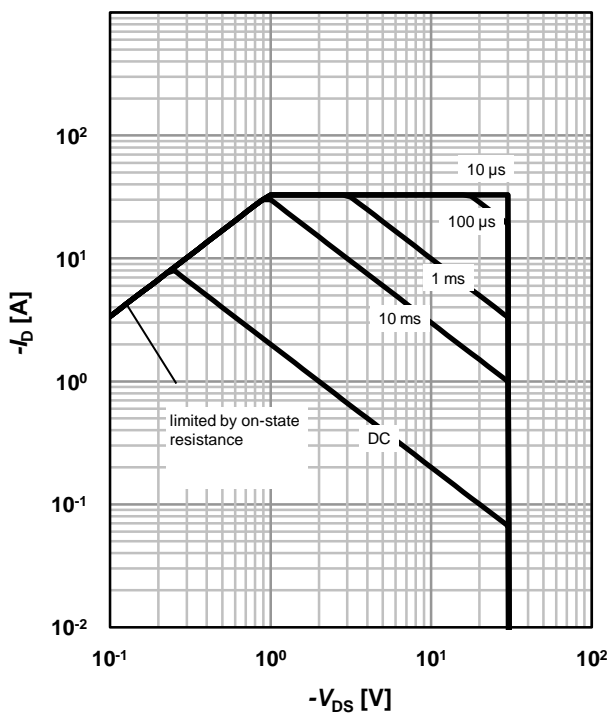
$I_D=f(T_A); |V_{GS}|\geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25\text{ °C}^1; D=0$

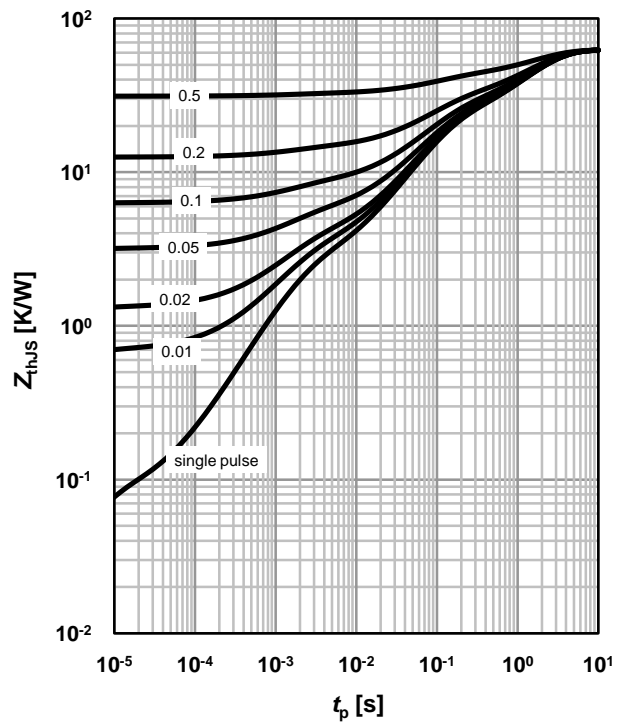
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJS}=f(t_p)$

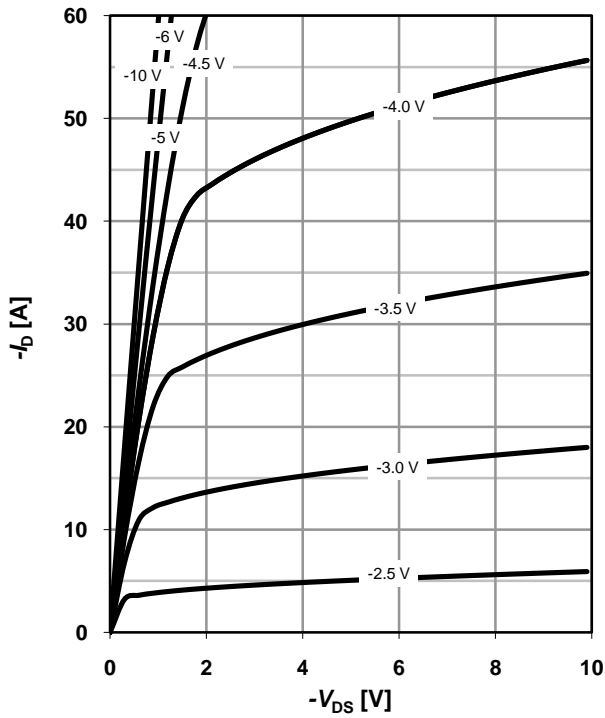
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

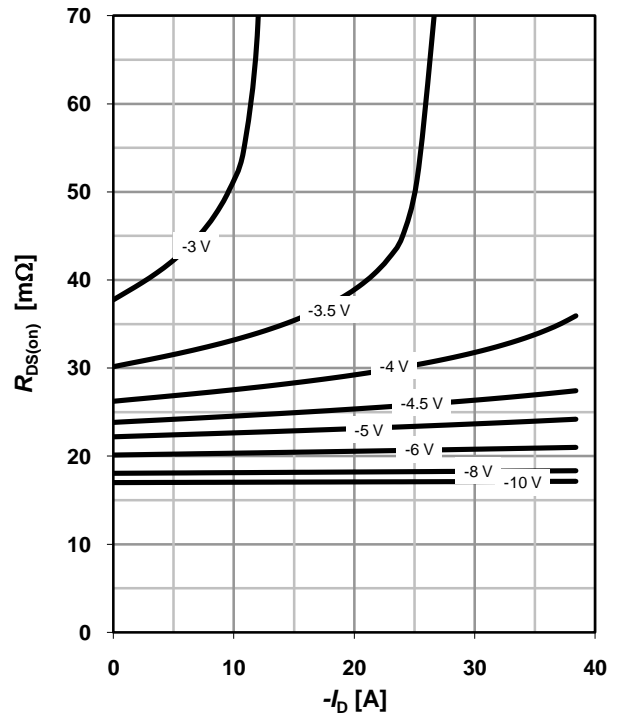
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

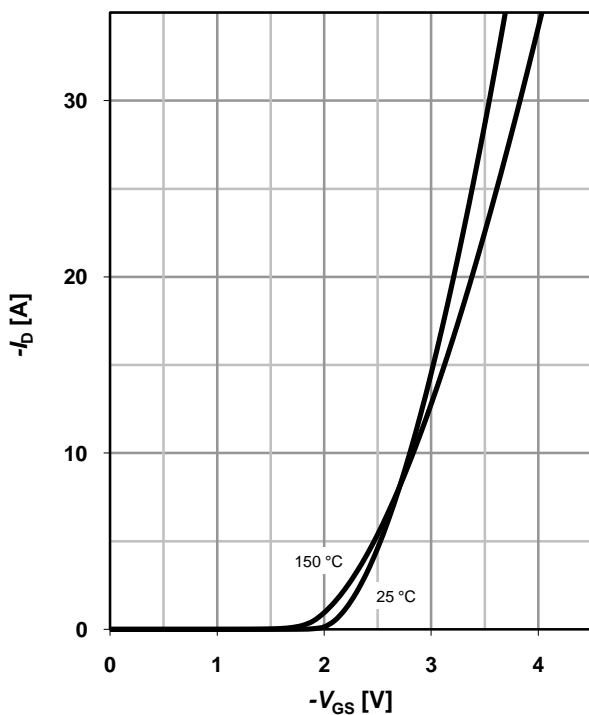
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

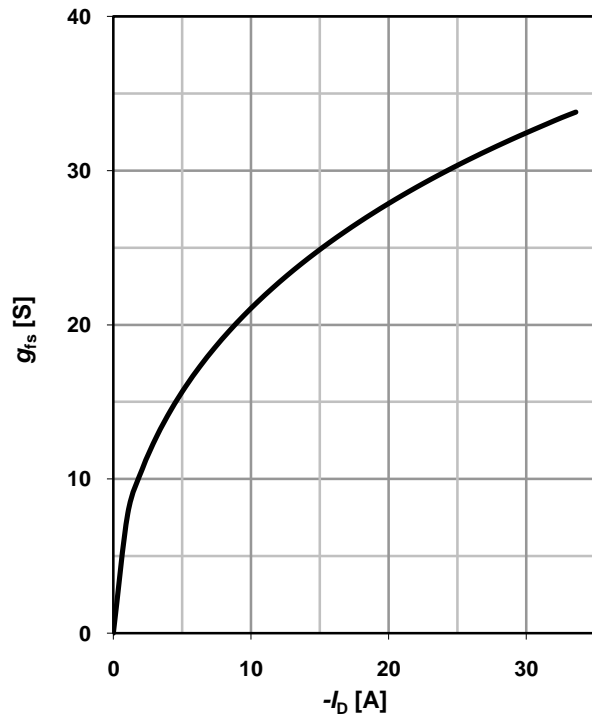
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



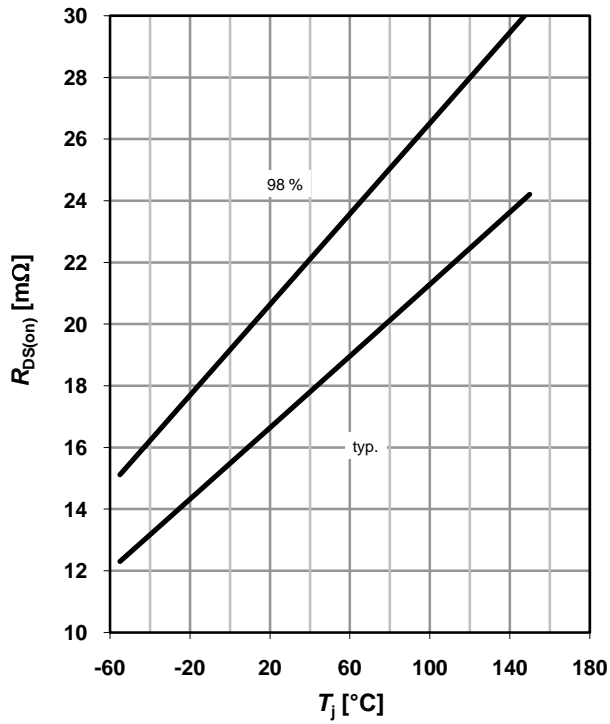
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



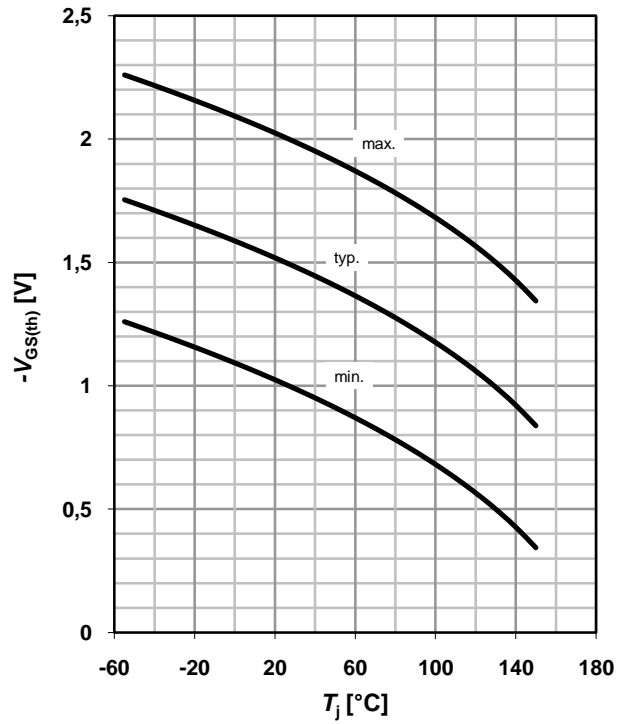
**9 Drain-source on-state resistance**

$R_{DS(on)}=f(T_j); I_D=-8.2\text{ A}; V_{GS}=-10\text{ V}$



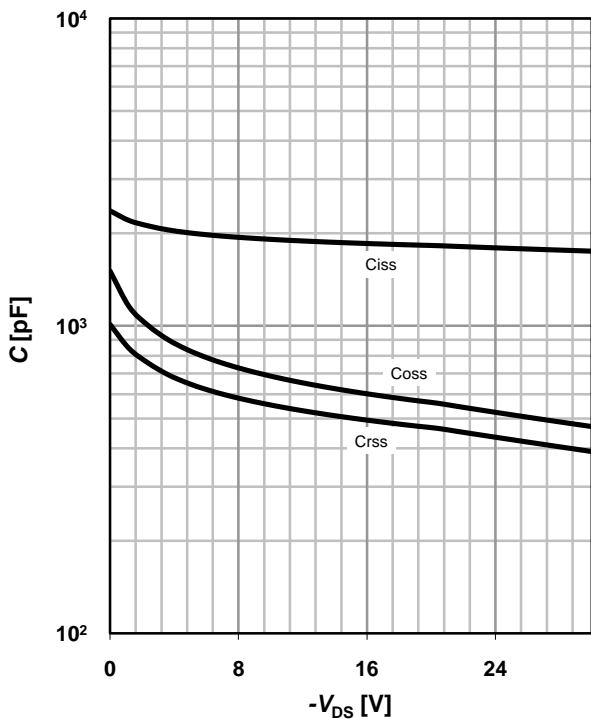
**10 Typ. gate threshold voltage**

$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}; I_D=-100\ \mu\text{A}$



**11 Typ. capacitances**

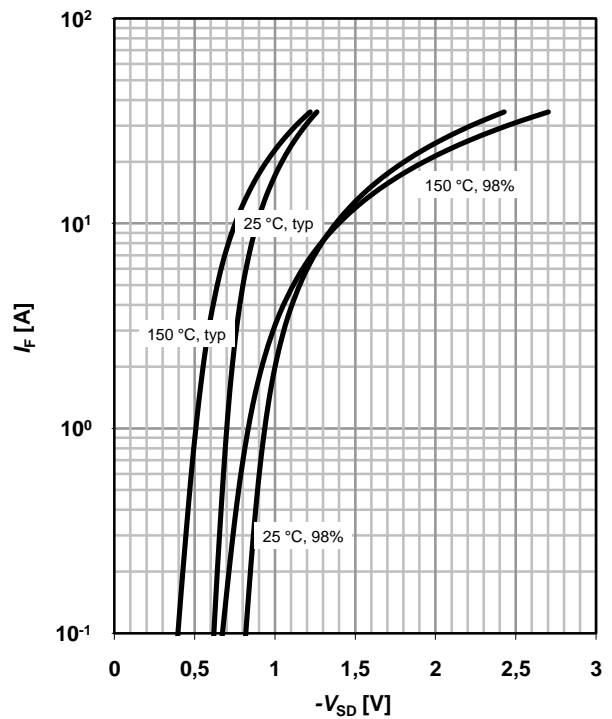
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

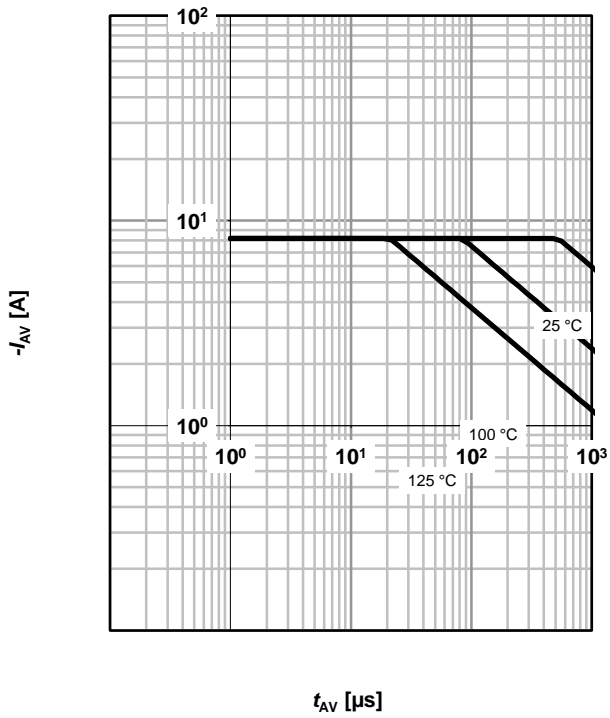
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

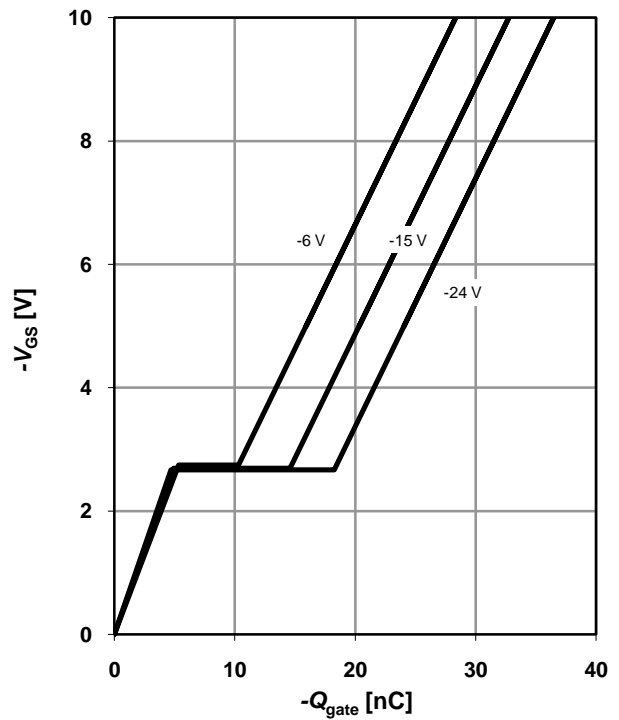
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

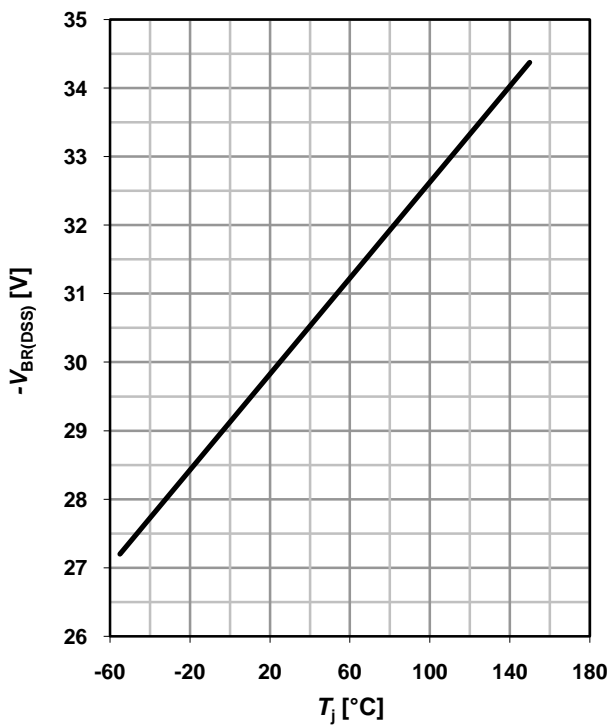
$V_{GS}=f(Q_{\text{gate}}); I_D=-8.2 \text{ A pulsed}$

parameter:  $V_{DD}$



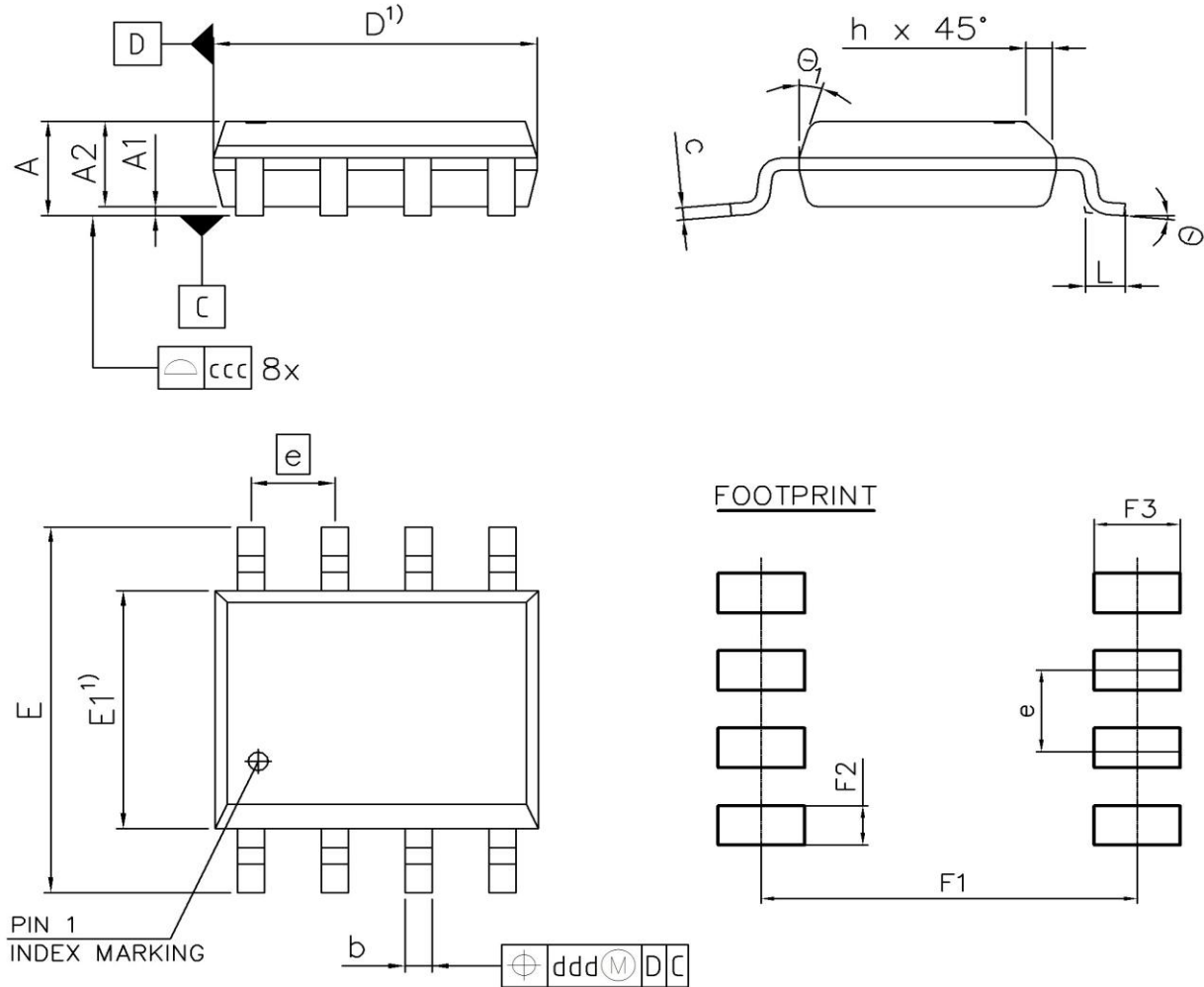
**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=-250 \mu\text{A}$



Package Outline

PG-DSO-8: Outline



1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
Θ	0°	8°	0°	8°
Θ <sub>1</sub>	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

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